Supporting Information

Low-leakage fiber-based field-effect transistors with an Al2O3-MgO nanolaminate as gate insulator

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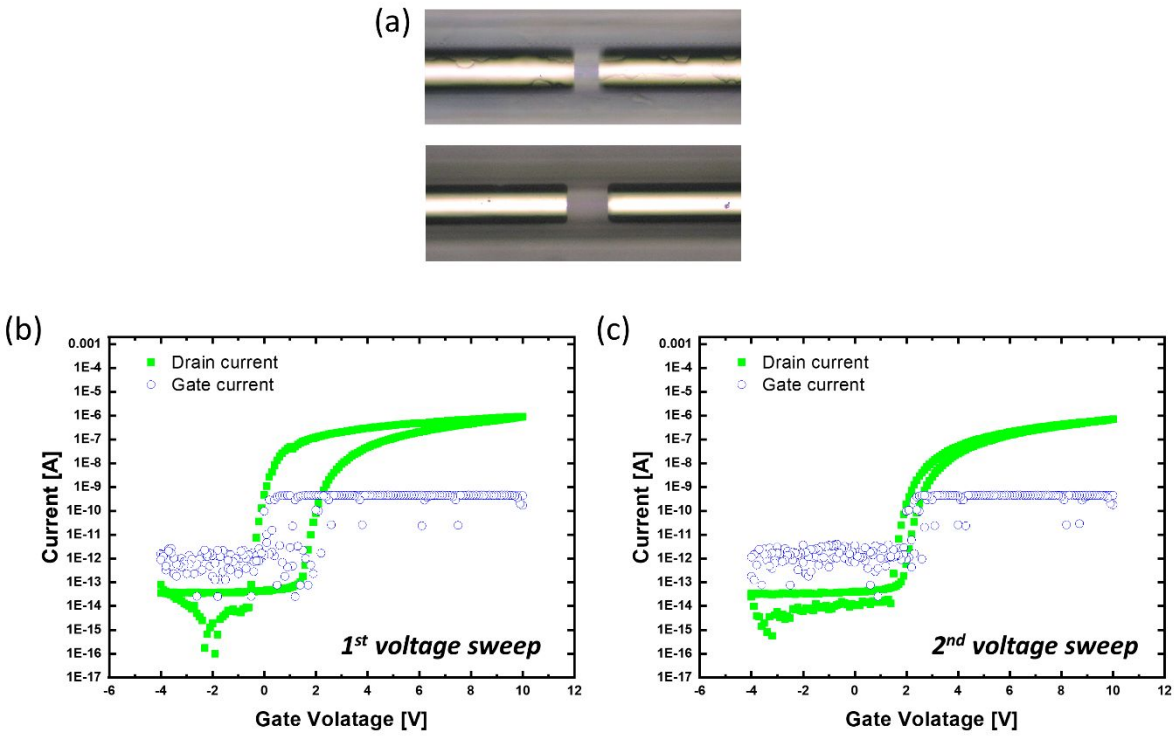

Figure S1. a) Microscopic images of the surfaces of fibers planarized by SU-8 2000.5/Al2O3 (top) and PVA/Al2O3 (bottom). 40-nm-thick Ti electrodes were deposited on the planarized fibers to appear the surface morphologies of the fibers explicitly. Changes of transfer curves of fiber-based TFTs b) at the first sweep and c) thereafter.